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(71) Applicant (for all designated States except US): SEMI-
CONDUCTOR ENERGY LABORATORY CO., LTD.
[JP/JP]; 398, Hase, Atsugi-shi, Kanagawa 2430036 (JP).

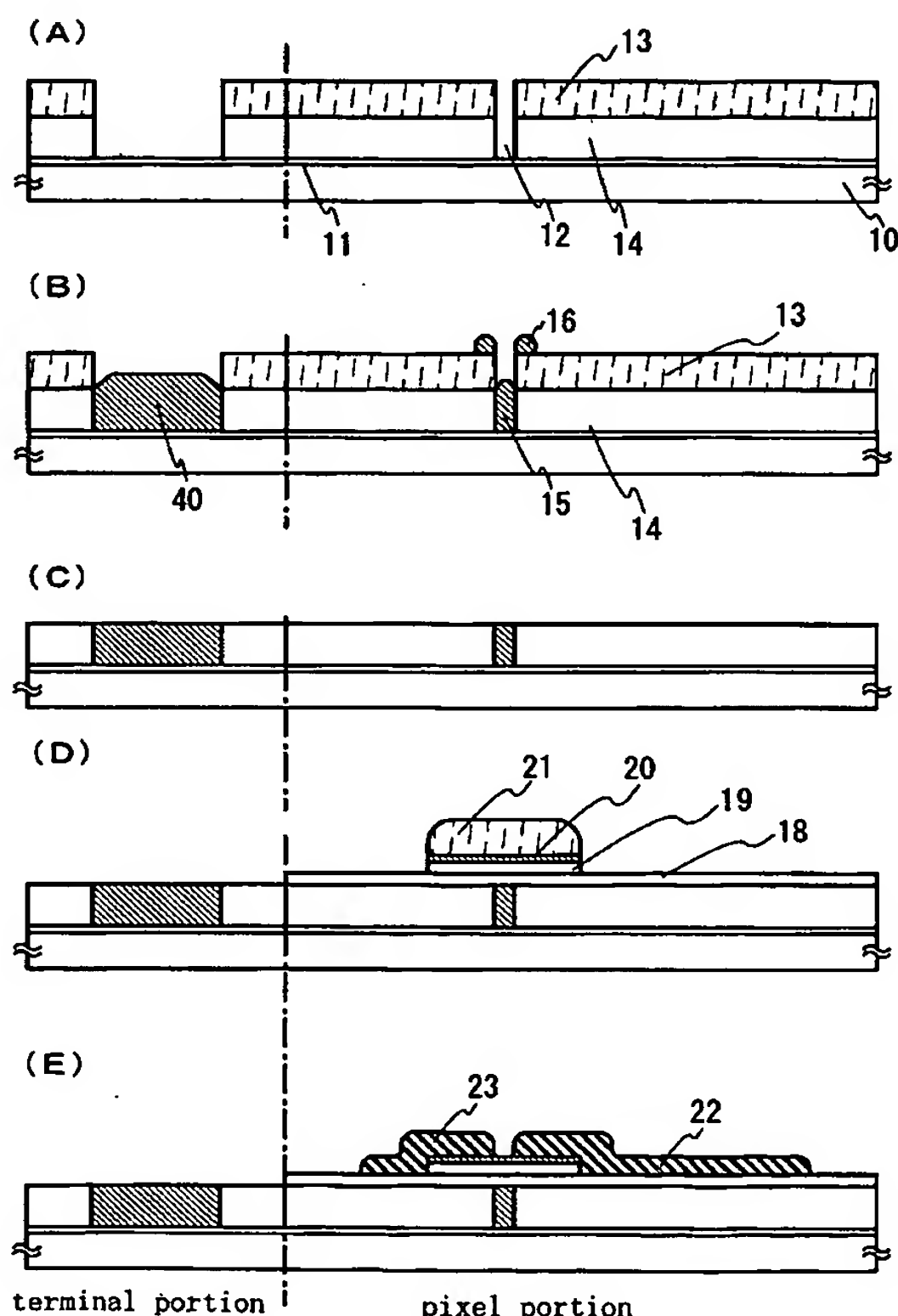
(72) Inventors; and

(75) Inventors/Applicants (for US only): KUWABARA,
Hideaki [JP/JP]; c/o SEMICONDUCTOR ENERGY
LABORATORY CO., LTD., 398, Hase, Atsugi-shi, Kana-
gawa 2430036 (JP). YAMAZAKI, Shunpei [JP/JP]; c/o
SEMICONDUCTOR ENERGY LABORATORY CO.,
LTD., 398, Hase, Atsugi-shi, Kanagawa 2430036 (JP).
MAEKAWA, Shinji [JP/JP]; c/o SEMICONDUCTOR
ENERGY LABORATORY CO., LTD. 398, Hase, At-
sugi-shi, Kanagawa 2430036 (JP). NAKAMURA, Osamu
[JP/JP]; c/o SEMICONDUCTOR ENERGY LABORA-
TORY CO., LTD., 398, Hase, Atsugi-shi., Kanagawa
2430036 (JP).

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(54) Title: ELECTRONIC DEVICE AND SEMICONDUCTOR DEVICE AND METHOD FOR MANUFACTURING THE SAME



(57) Abstract: It is conceivable that the problem that a signal is delayed by resistor of a wiring in producing a display which displays large area becomes remarkable. The present invention provides a manufacturing process using a droplet discharge method suitable for a large-sized substrate. In the present invention, after forming a base layer 11 (or base pretreatment) which enhances adhesiveness over a substrate in advance and forming an insulating film, a mask having a desired pattern shape is formed, and a desired depression is formed by using the mask. A metal material is filled in the depression having a mask 13 and a sidewall made from an insulating film by a droplet discharge method to form an embedded wiring (a gate electrode, a capacitor wiring, lead wiring or the like). Afterwards, it is flattened by a planarization processing, for example, a press or a CMP processing.



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